

DSF8025SE/DSF8025SG

Fast Recovery Diode

DS6153-1 July 2014 (LN31793)

FEATURES

- Double Side Cooling
- High Surge Capability
- Low Recovery Charge

APPLICATIONS

- Induction Heating
- High Frequency Rectification
- Snubber, Antiparallel and FWD for GTO

VOLTAGE RATINGS

Part and Ordering Number	Repetitive Peak Voltages V _{RRM} V	Conditions
DSF8025SE25	2500	
DSF8025SG25		$V_{RSM} = V_{RRM} + 100V$
DSF8025SE24	2400	
DSF8025SG24		
DSF8025SE23	2300	
DSF8025SG23		
DSF8025SE22	2200	
DSF8025SG22		
DSF8025SE21	2100	
DSF8025SG21		
DSF8025SE20	2000	
DSF8025SG20		

Lower voltage grades available.

KEY PARAMETERS

V_{RRM}	2500V
I _{F(AV)}	650A
I _{FSM}	7500A
Q_r	540μC
t _{rr}	5.0μs

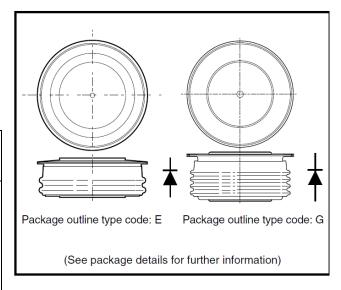


Fig. 1 Package outline

ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

DSF8025SE20 for a 2000V device in an "E" outline

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order

CURRENT RATINGS

Symbol	Parameter	Test Conditions	Max.	Units			
Double Si	Double Side Cooled						
I _{F(AV)}	Mean forward current	Half wave resistive load T _{case} = 65°C	650	Α			
I _{F(RMS)}	RMS value	T _{case} = 65°C -	1020	Α			
I _F	Continuous (direct) on-state current	T _{case} = 65°C -	785	Α			
Single Side Cooled (Anode side)							
I _{F(AV)}	Mean forward current	Half wave resistive load T _{case} = 65°C -	385	Α			
I _{F(RMS)}	RMS value	T _{case} = 65°C	604	Α			
I _F	Continuous (direct) on-state current	T _{case} = 65°C	465	Α			

SURGE RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
I _{FSM}	Surge (non-repetitive) on-state current	10ms half sine, T _{case} = 150°C	6.0	kA
l ² t	I ² t for fusing	$V_R = 50\% V_{RRM}$	180	kA ² s
I _{FSM}	Surge (non-repetitive) on-state current	10ms half sine, T _{case} = 150°C	7.5	kA
l ² t	I ² t for fusing	$V_R = 0$	281	kA ² s

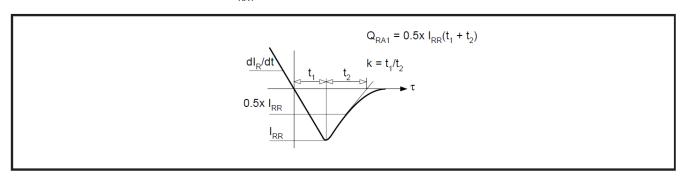
THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Conditions		Min.	Max.	Units
R _{th(j-c)}	Thermal resistance – junction to case	Double side cooled	DC	-	0.047	°C/W
		Single side cooled	Anode DC	-	0.094	°C/W
			Cathode DC	-	0.094	°C/W
R _{th(c-h)}	Thermal resistance – case to heatsink	Clamping force 8.0kN	Double side	-	0.018	°C/W
		(with mounting compound)	Single side	-	0.036	°C/W
T _{vj}	Virtual junction temperature	On-state (conducting)		-	150	°C
		Reverse (blocking)		-	150	°C
T _{stg}	Storage temperature range			-55	175	°C
F _m	Clamping force			7.0	9.0	kN

CHARACTERISTICS

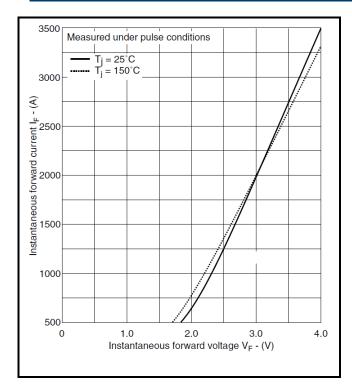
Symbol	Parameter	Test Conditions	Тур.	Max.	Units
V_{FM}	Forward voltage	At 1000A peak, T _{case} = 25°C	-	2.3	V
I _{RM}	Peak reverse current	At V _{DRM} , T _{case} = 150°C	-	50	mA
t _{rr}	Reverse recovery time	I _F = 750A, dI _{RR} /dt =100A/μs T _{case} =125°C, V _R =100V		5.0	μS
Qs	Total stored charge		-	540	μC
I _{rr}	Peak reverse recovery current			235	Α
K	Softness Factor		1.8	-	-
V_{TO}	Threshold voltage	At T _{vj} = 150°C	-	1.48	V
r _T	Slope resistance	At T _{vj} =150°C	-	0.8	mΩ
V_{FRM}	Forward recovery voltage	Di/dt = 1000A/us, T _j = 125°C	70		V

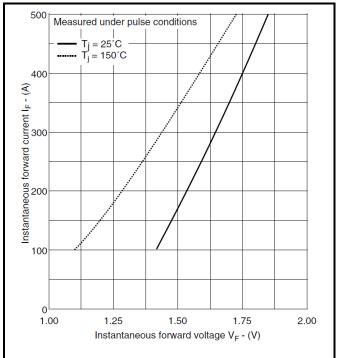
DEFINITION OF K FACTOR AND \mathbf{Q}_{RA1}



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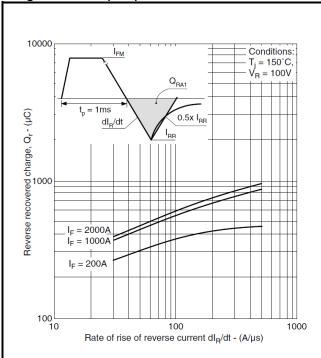


Fig.4 Recovered charge

Fig.3 Maximum (limit) on-state characteristics

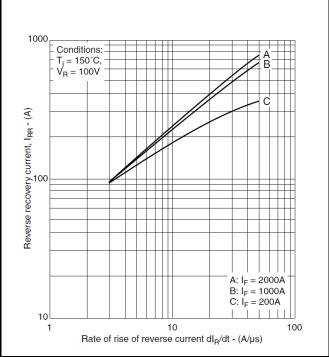


Fig.5 Typical reverse recovery current

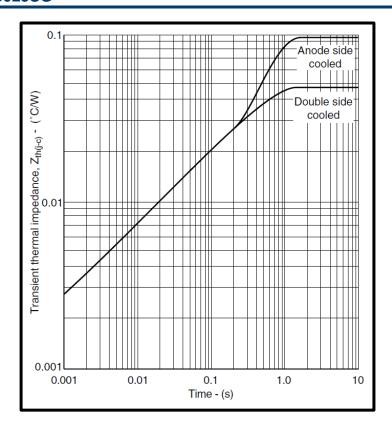


Fig.6 Maximum (limit) transient thermal impedance- junction to case

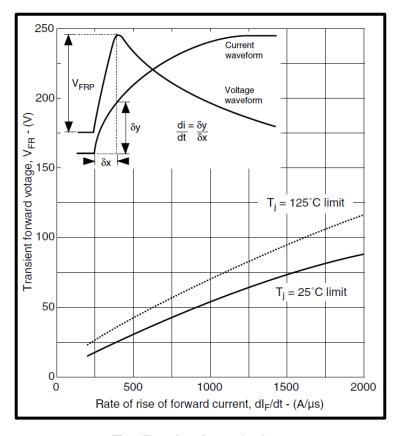


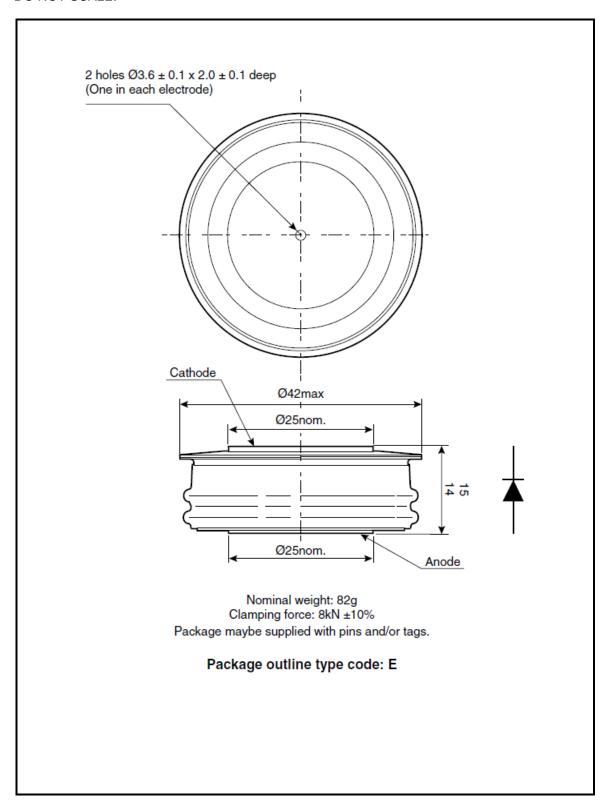
Fig.7 Transient forward voltage

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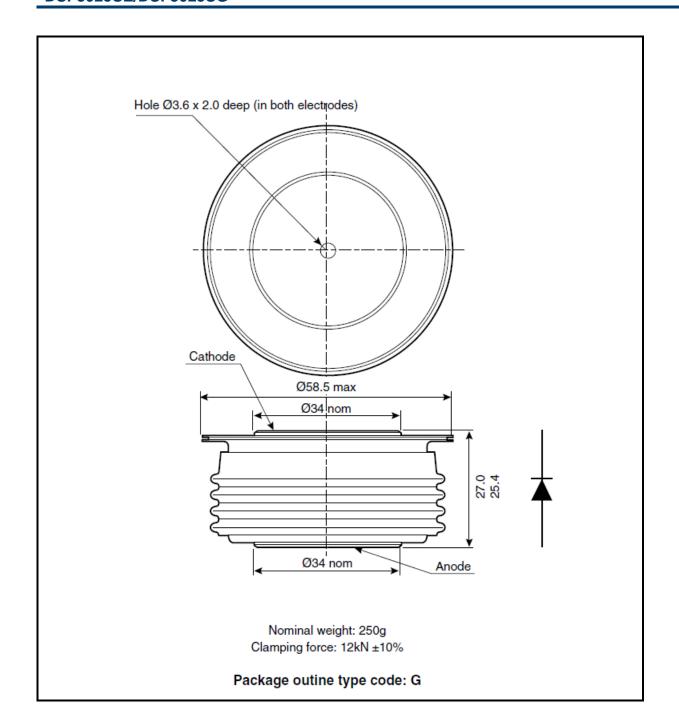
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PACKAGE DETAILS

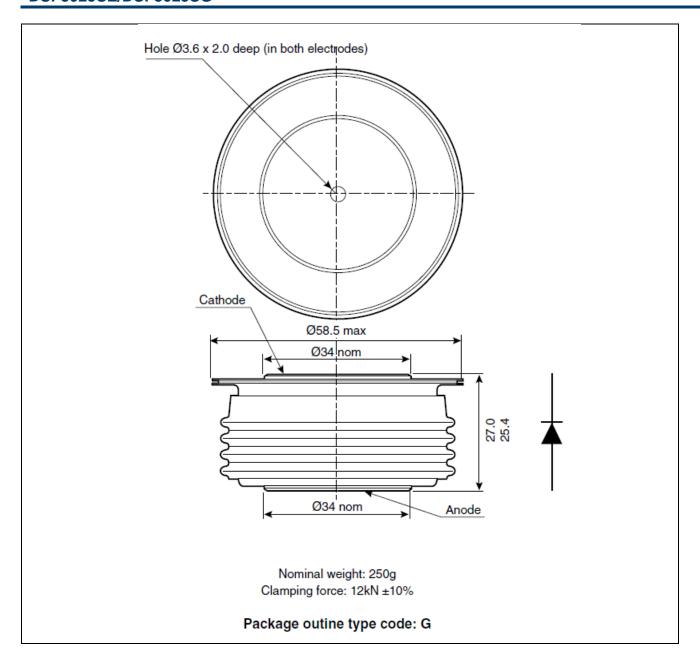
For further package information, please contact Customer Services. All dimensions in mm, unless stated otherwise. DO NOT SCALE.



Note: Some packages may be supplied with gate and or tags.



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